

# Synthesis of Graphene by Plasma Enhanced Chemical Vapor Deposition and Its transfer for Device Application

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In this report, we present a very effective growing method of graphene using plasma enhanced chemical vapor deposition(PECVD). The graphene is successfully grown on copper substrate. Low temperature growing is obtained with methane and hydrogen plasma. The graphene layers are analyzed by Raman spectroscopy and atomic force microscope. We also provide a transfer technique of graphene layer onto silicon substrate to build up various kinds of application devices.